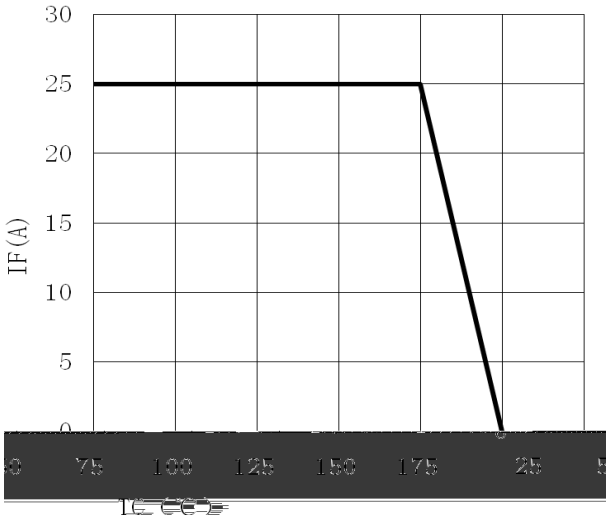
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
Maximum RMS Voltage	V_{RMS}	140	V
Maximum DC Blocking Voltage	V_{DC}	200	V
Maximum Average Forward Current	I_F	4 × 25	A
Peak forward surge current	I_{FSM}	400	A
Typical Thermal Resistance Junction to Case	$R_{\theta Jc}$	2.2	/W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	I_R=1mA	200			V
Forward Voltage	V_F	I_F=5A T_C=25		0.85	0.95	V
		I_F=5A T_C=125		0.69	0.85	
		I_F=12.5A T_C=25		1.05	1.35	
		I_F=12.5A T_C=125		0.85	1.05	
Instantaneous Reverse Current	I_R Note 1	V_R=200V T_a=25			10	μA
		V_R=200V T_a=125			500	
Reverse Recovery Time	t_{rr}	I_F=0.5A I_R=1.0A I_{RR}=0.25A		35	50	ns

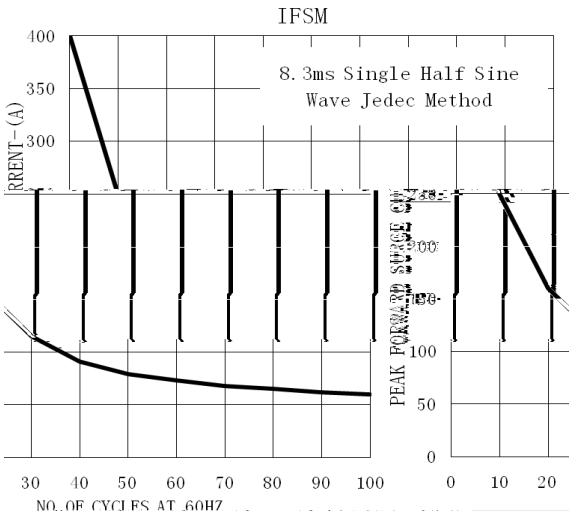
Notes

1. Short duration pulse test used to minimize self-heating effect.
2. Unless otherwise noted, values for the parameters of a single chip

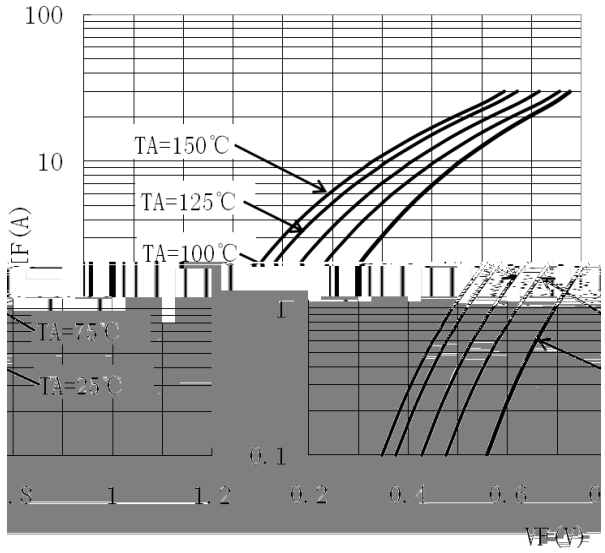
IF - TC



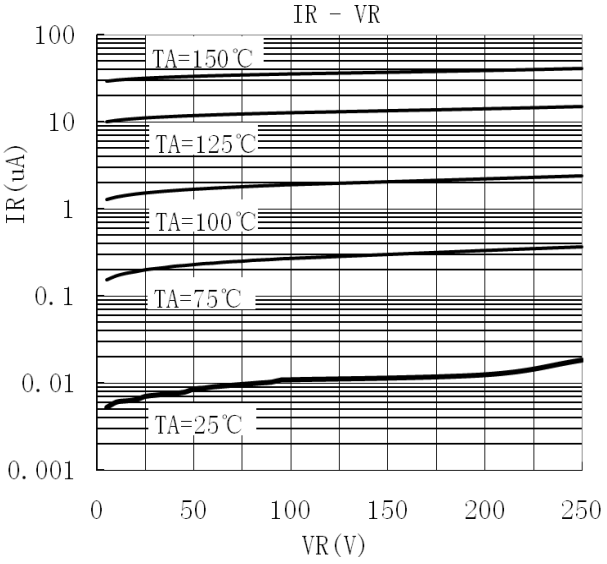
IFSM



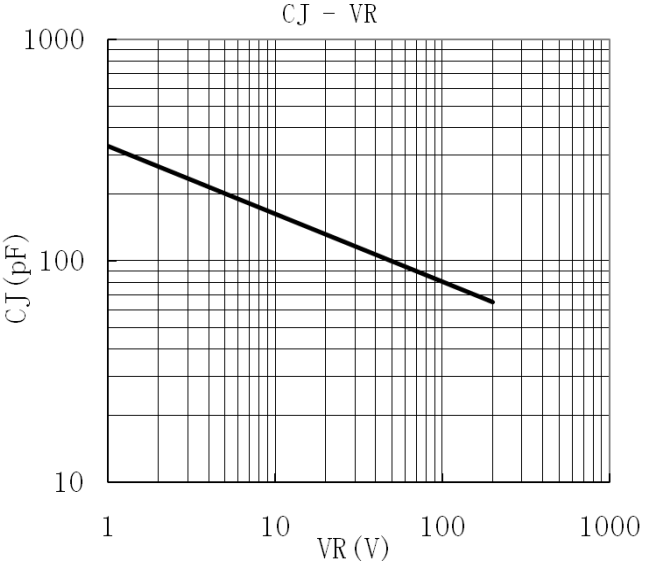
IF - VF



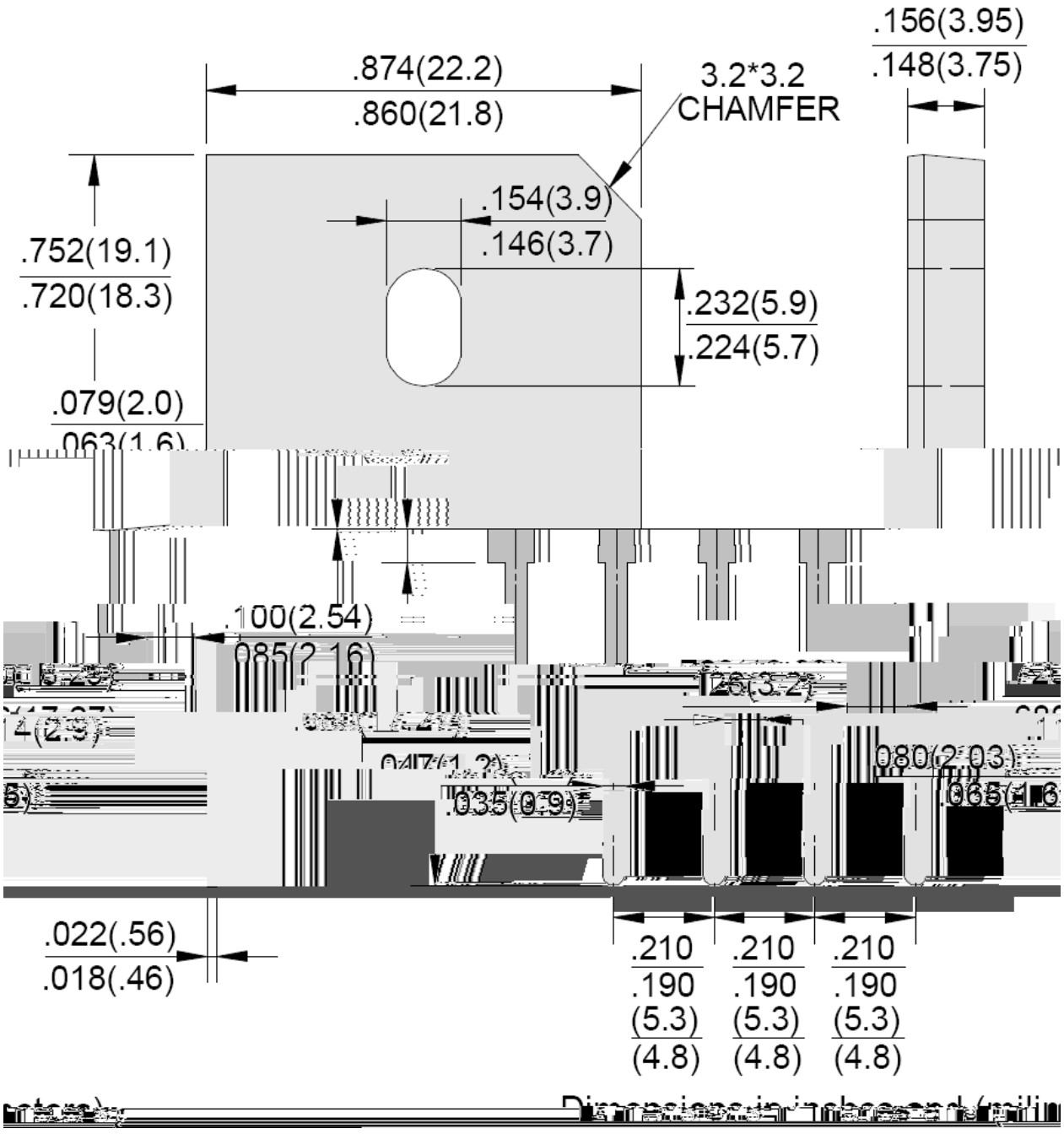
IR - VR



CJ - VR



GBU


.156(3.95)
.148(3.75)
.874(22.2)
.860(21.8)
3.2*3.2
CHAMFER
.154(3.9)
.146(3.7)
.752(19.1)
.720(18.3)
.232(5.9)
.224(5.7)
.079(2.0)
.100(2.54)
.035(0.9)
.022(.56)
.018(.46)
.210
.190
(5.3)
(4.8)
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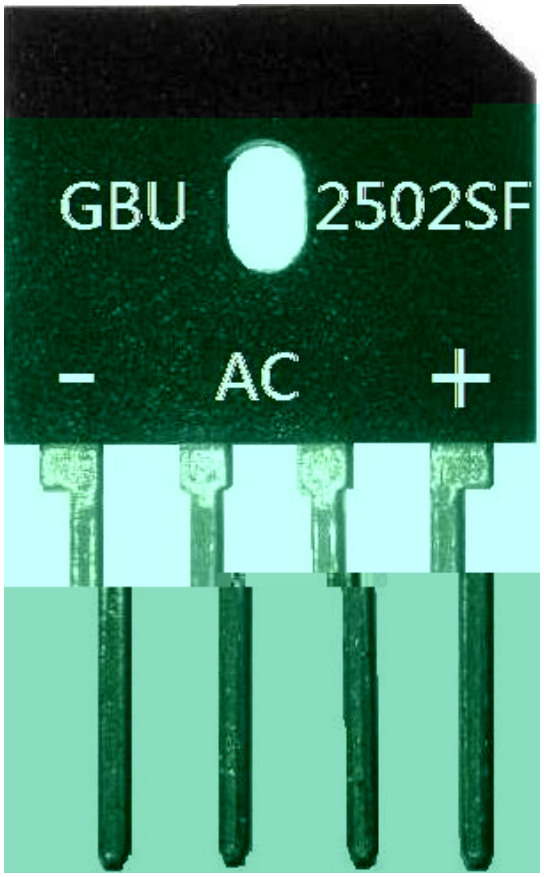
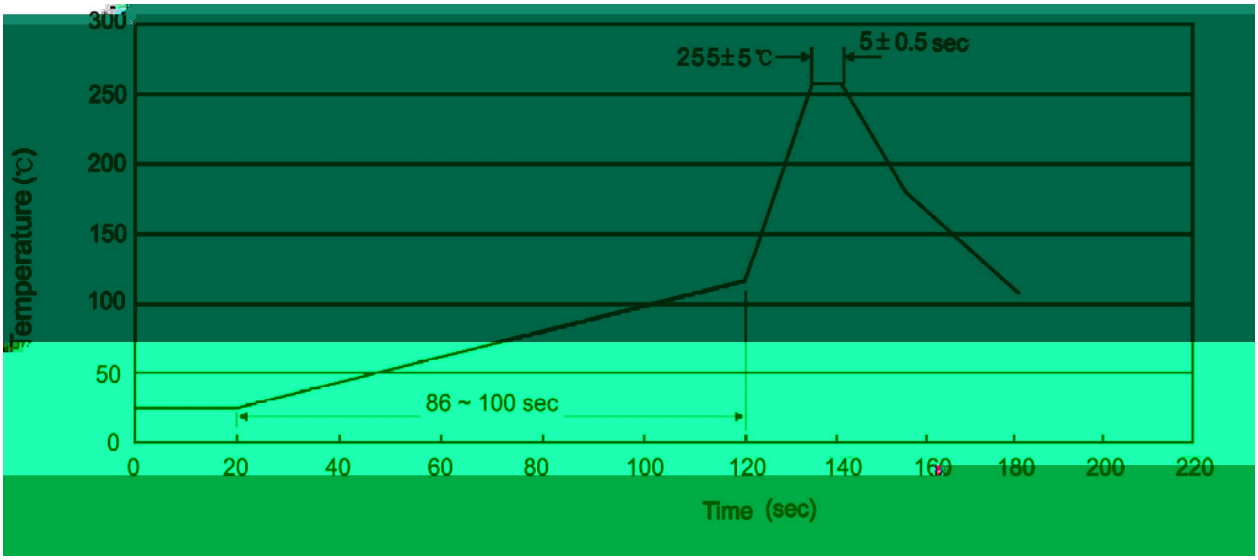
(5.3)
(4.8)



GBU2502SF

Note:

GBU2502SF Product Type



					Note:
1	25	150	60	90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255	5	5	0.5sec;	2.Peak Temp.:255 5 , Duration:5 0.5sec.
3					